
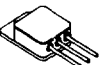


NEW ENGLAND SEMICONDUCTOR

BIPOLAR POWER TRANSISTOR NPN PLANAR

PACKAGE	DEVICE TYPE	BV_{CEO} VOLTS	PEAK I_C AMPS	h_{FE} min/max	$I_C @ V_{CE}$ A V	$V_{CE(sat)}$ max VOLTS	$I_C @ I_B$ A A
NPN TO-254 	2N7368	80	10.0	30-140	30.0/2.0	1.0	5.0/0.5
	NSP4070	100	10.0	40-120	5.0/5.0	0.8	5.0/0.5
	NSP4071	150	10.0	40-120	5.0/5.0	0.8	5.0/0.5
	NSP5622	60	10.0	70-200	5.0/5.0	1.1	5.0/0.5
	NSP5624	80	10.0	30-90	5.0/5.0	1.1	5.0/0.5
	NSP5626	80	10.0	70-200	5.0/5.0	1.1	5.0/0.5
	NSP5628	100	10.0	30-90	5.0/5.0	1.1	5.0/0.5
	NSP6274	100	50.0	30-200	20.0/4.0	1.5	20.0/0.2
	NSP6275	120	50.0	30-200	20.0/4.0	1.5	20.0/0.2
	NSP6276	140	50.0	30-200	20.0/4.0	1.5	20.0/0.2
	NSP6277	150	50.0	30-200	20.0/4.0	1.5	20.0/0.2
	NSP6338	150	25.0	30-120	10.0/2.0	1.2	10.0/1.0
	NSP6339	120	25.0	30-120	10.0/2.0	1.2	10.0/1.0
	NSP6340	140	25.0	30-120	10.0/2.0	1.2	10.0/1.0
	NSP6341	150	25.0	30-120	10.0/2.0	1.2	10.0/1.0

PNP PLANAR

PNP TO-254 	2N7369	80	10.0	30-140	3.0/2.0	1.0	5.0/0.5
	NSP5741	60	20.0	20-80	10.0/5.0	1.75	10.0/1.0
	NSP5742	100	20.0	20-80	10.0/5.0	1.75	10.0/1.0
	NSP6246	60	15.0	20-100	7.0/5.0	2.8	15.0/1.5
	NSP6247	80	15.0	20-100	6.0/5.0	3.8	15.0/1.5